Panasonic ICP II	PROCESS RECIPE	101
	TITTLE	SiOx Vert
	COMMENT	Vertical etch
	END STEP	5

Wafer pushing for neutralization	DO
Start step for neutralization	4
C-HE start flow rate	30
HE vacuum completion pressure	30

Gas flow	limit		unit	STEP1	STEP2	STEP3	STEP4	STEP5	STEP6	STEP7
A: BCl3	0	%	cm3/min	0	0	0	0	0	0	0
B:Cl2	20	%	cm3/min	0	0	0	0	0	0	0
C: CF4	20	%	cm3/min	0	0	0	0	0	0	0
D:O2	0	%	cm3/min	0	0	0	0	0	0	0
E:CHF3	20	%	cm3/min	40	40	40	0	0	0	0
F:N2	20	%	cm3/min	0	0	0	100	100	0	0
Pressure			Pa	2	0.5	0.5	2.5	2.5	0	0
Pressure limit			%	20	20	20	20	20	0	0
Step time			min:sec	00:02.0	00:05.0	enter time	00:05.0	00:05.0	0	0
Chamber dead time			min:sec	00:05.0	00:05.0	00:05.0	00:05.0	00:05.0	0	0
RF source wait time			min:sec	00:15.0	00:00.0	00:00.0	00:00.0	00:00.0	0	0
Vacuuming time			min:sec	00:10.0	00:00.0	00:30.0	00:00.0	00:00.0	0	0
RF (source) FWD	20	%	W	900	900	900	100	50	0	0
RF (source) REF limit			W	25	25	25	25	25	0	0
RF(BIAS) FWD	20	%	W	0	0	200	0	0	0	0
RF(BIAS) REF limit			W	0	0	12	0	0	0	0
C-HE flow rate	20	%	cm3/min	15	15	15	0	0	0	0
C-HE pressure	20	%	Pa	700	700	700	0	0	0	0
Use of ESC				DO	DO	DO	DO NOT	DO NOT	DO NOT	DO NOT
ESC VOLT1	20	%	V	1200	1200	1200	0	0	0	0
ESC VOLT2	20	%	V	NEG. 1200	NEG. 1200	NEG. 1200	0	0	0	0
ESC CURR1			uA	200	200	200	0	0	0	0